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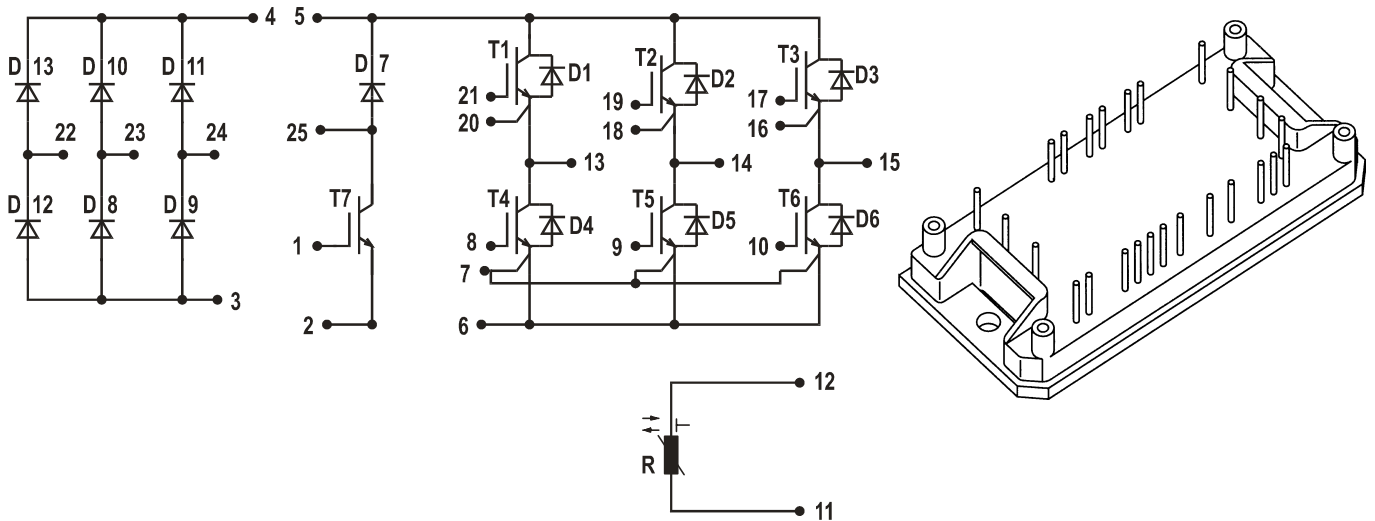
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# Converter - Brake - Inverter Module (CBI1)



Rectifier	Brake	Inverter
$V_{RRM} = 1200V$	$V_{CES} = 600 V$	$V_{CES} = 600 V$
$I_{FAVM} = 11 A$	$I_{C25} = 7 A$	$I_{C25} = 7 A$
$I_{FSM} = 250 A$	$V_{CE(sat)} = 2.0 V$	$V_{CE(sat)} = 2.0 V$

### Input Rectifier Bridge D8 - D13

Symbol	Conditions	Maximum Ratings	
$V_{RRM}$		1200	V
$I_F$	$T_{VJ} = 25^{\circ}C$	36	A
$I_{FAVM}$	$T_{VJ} = 150^{\circ}C; T_K = 70^{\circ}C$	11	A
$I_{FSM}$	$T_{VJ} = 45^{\circ}C; t = 10 \text{ ms sine } 50 \text{ Hz}$	250	A
$i^2t$	$T_{VJ} = 125^{\circ}C$	310	A <sup>2</sup> s
$T_{VJ}$		+150	°C

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}C$ , unless otherwise specified)		
		min.	typ.	max.
$I_R$	$V_{RRM} = 1200 V; T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$			10 $\mu A$ 3 mA
$V_F$	$I_F = 36 A$		1.15	1.4 V
$R_{thJC}$	per die		1.4	°C/W

### Features

- NPT IGBT technology
- Square RBSOA, no latchup
- Free wheeling diodes with Hiperfast and soft recovery behaviour
- Isolation voltage 2500 V~
- Built in temperature sense
- High level of integration: one module for complete drive system
- **Direct Copper Bonded** Al<sub>2</sub>O<sub>3</sub> ceramic base plate

### Applications

- AC motor control
- AC servo and robot drives

### Advantages

- No need of external isolation
- Easy to mount with two screws
- Package designed for wave soldering
- High temperature and power cycling capability

IXYS reserves the right to change limits, test conditions and dimensions.

**Output Inverter T1 - T6, D1 - D6**

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$	600	V
$V_{CGR}$	$T_{VJ} = 25^{\circ}\text{C}; R_{GE} = 20\text{k}\Omega$	600	V
$V_{GE}$	$T_{VJ} = 25^{\circ}\text{C}$	$\pm 20$	V
$I_C$	$T_C = 25^{\circ}\text{C}$	7	A
	$T_C = 90^{\circ}\text{C}$	4.5	A
$I_{CM}$	$t_p = 1 \text{ ms} = 1\% \text{ duty cycle}; T_C = 25^{\circ}\text{C}$	14	A
		$T_C = 90^{\circ}\text{C}$	9
$t_{SC}$	IGBT $V_{CE} = 600 \text{ V}; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	38	W
$T_{VJ}$	Free-Wheeling Diode	+150	$^{\circ}\text{C}$
$T_{VJ}$	IGBT	+150	$^{\circ}\text{C}$

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)				
		min.	typ.	max.		
$I_{CES}$	$V_{GE} = 0 \text{ V}; V_{CE} = 600 \text{ V}$			10 $\mu\text{A}$		
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = 25 \text{ V}$			100 nA		
$V_{GE(th)}$	$V_{GE} = V_{CE}; I_C = 0.2 \text{ mA}$	3	4	5 V		
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}; I_C = 0.5 \text{ mA}; T_{VJ} = -40^{\circ}\text{C}$	600		V		
$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}; I_C = 4 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		2.0	2.5 V		
			2.3	2.8 V		
$t_f$	Inductive load, $T_{VJ} = 150^{\circ}\text{C}$ $V_{CC} = 400 \text{ V}; I_C = 4 \text{ A}$ $R_G = 50 \Omega; V_{GE} = \pm 15 \text{ V}$		100	150 ns		
		$t_r$		20	30 ns	
$t_{d(on)}$				20	30 ns	
		$t_{d(off)}$		260	390 ns	
$E_{off}$				0.1	0.13 mJ	
		$E_{on}$		0.2	0.26 mJ	
$C_{iss}$			$V_{GE} = 0 \text{ V}$ $V_{CE} = 25 \text{ V}$ $f = 1 \text{ MHz}$		270	340 pF
		$C_{oss}$			30	40 pF
				$C_{riss}$		18
$g_{fs}$		$V_{CE} = 20 \text{ V}; I_C = 4 \text{ A}$	0.8	3.2	S	
$Q_g$	$V_{CC} = 400 \text{ V}; I_C = 6 \text{ A pulse}; V_{GE} = 15 \text{ V}$		24	nC		
$V_F$	$I_F = 10 \text{ A}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		2	V		
			1.8	V		
$t_{rr}$	$I_F = 10 \text{ A}; V_R = -300 \text{ V}; V_{GE} = 0 \text{ V}$ $di_F/dt = -350 \text{ A}/\mu\text{s}; T_{VJ} = 100^{\circ}\text{C}$		0.2	$\mu\text{s}$		
$Q_r$	$I_F = 10 \text{ A}; V_R = -300 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $di_F/dt = -350 \text{ A}/\mu\text{s}; V_{GE} = 0 \text{ V}; T_{VJ} = 125^{\circ}\text{C}$		0.3	$\mu\text{C}$		
			0.9	$\mu\text{C}$		
$I_r$				250 $\mu\text{A}$		
$R_{thJC}$	IGBT (per die)		2.7	$^{\circ}\text{C}/\text{W}$		
	Diode (per die)		2.3	$^{\circ}\text{C}/\text{W}$		

**Brake Chopper T7, D7**

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$	600	V
$V_{CGR}$	$T_{VJ} = 25^{\circ}\text{C}; R_{GE} = 20\text{k}\Omega$	600	V
$V_{GE}$	$T_{VJ} = 25^{\circ}\text{C}$	$\pm 20$	V
$I_C$	$T_C = 25^{\circ}\text{C}$	7	A
	$T_C = 90^{\circ}\text{C}$	4.5	A
$I_{CM}$	$t_p = 1 \text{ ms} = 1\% \text{ duty cycle}; T_C = 25^{\circ}\text{C}$	14	A
		$T_C = 90^{\circ}\text{C}$	9
$t_{SC}$	IGBT $V_{CE} = 600 \text{ V}; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	38	W
$T_{VJ}$	Free-Wheeling Diode	+150	$^{\circ}\text{C}$
$T_{VJ}$	IGBT	+150	$^{\circ}\text{C}$

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)				
		min.	typ.	max.		
$I_{CES}$	$V_{GE} = 0 \text{ V}; V_{CE} = 600 \text{ V}$			20 $\mu\text{A}$		
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = 25 \text{ V}$			100 nA		
$V_{GE(th)}$	$V_{GE} = V_{CE}; I_C = 0.2 \text{ mA}$	3	4	5 V		
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}; I_C = 0.5 \text{ mA}; T_{VJ} = -40^{\circ}\text{C}$	600		V		
$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}; I_C = 4 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		2.0	2.5 V		
			2.3	2.8 V		
$t_f$	Inductive load, $T_{VJ} = 150^{\circ}\text{C}$ $V_{CC} = 400 \text{ V}; I_C = 4 \text{ A}$ $R_G = 50 \Omega; V_{GE} = \pm 15 \text{ V}$		100	150 ns		
		$t_r$		20	30 ns	
$t_{d(on)}$			20	30 ns		
$t_{d(off)}$			260	390 ns		
$E_{off}$			0.1	0.13 mJ		
$E_{on}$			0.2	0.26 mJ		
$C_{iss}$		$V_{GE} = 0 \text{ V}$ $V_{CE} = 25 \text{ V}$ $f = 1 \text{ MHz}$		270	340 pF	
			$C_{oss}$		30	40 pF
			$C_{riss}$		18	23 pF
$g_{fs}$		$V_{CE} = 20 \text{ V}; I_C = 4 \text{ A}$	0.8	3.2	S	
$Q_g$	$V_{CC} = 400 \text{ V}; I_C = 6 \text{ A pulse}; V_{GE} = 15 \text{ V}$		24	nC		
$V_F$	$I_F = 10 \text{ A}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		2	V		
			1.8	V		
$t_{rr}$	$I_F = 10 \text{ A}; V_R = -300 \text{ V}; V_{GE} = 0 \text{ V}$ $di_F/dt = -350 \text{ A}/\mu\text{s}; T_{VJ} = 100^{\circ}\text{C}$		0.2	$\mu\text{s}$		
$Q_r$	$I_F = 10 \text{ A}; V_R = -300 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $di_F/dt = -350 \text{ A}/\mu\text{s}; V_{GE} = 0 \text{ V}; T_{VJ} = 125^{\circ}\text{C}$		0.3	$\mu\text{C}$		
			0.9	$\mu\text{C}$		
$I_r$				250 $\mu\text{A}$		
$R_{thJC}$	IGBT (per die)		2.7	$^{\circ}\text{C}/\text{W}$		
	Diode (per die)		2.3	$^{\circ}\text{C}/\text{W}$		



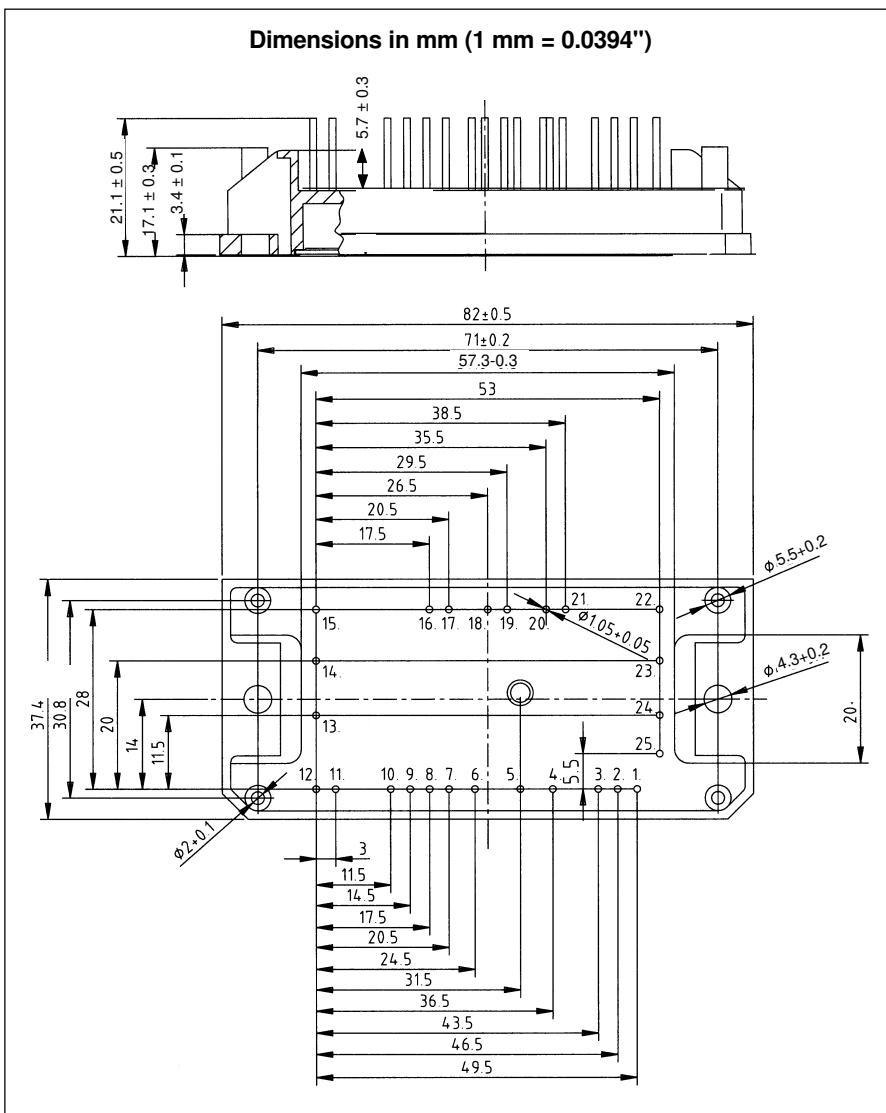
**Module**

Symbol	Conditions	Maximum Ratings	
$T_{stg}$		-40...+125	°C
$V_{ISOL}$	$I_{ISOL} \leq 1 \text{ mA}$ ; 50/60 Hz; $t = 1 \text{ min}$	2500	V~
$M_d$	Mounting torque (M4)	2.0 - 2.2 18 - 20	Nm lb.in.
$d_s$	Creepage distance on surface	12.7	mm
$d_A$	Strike distance in air	12.7	mm
Weight	typ.	42	g

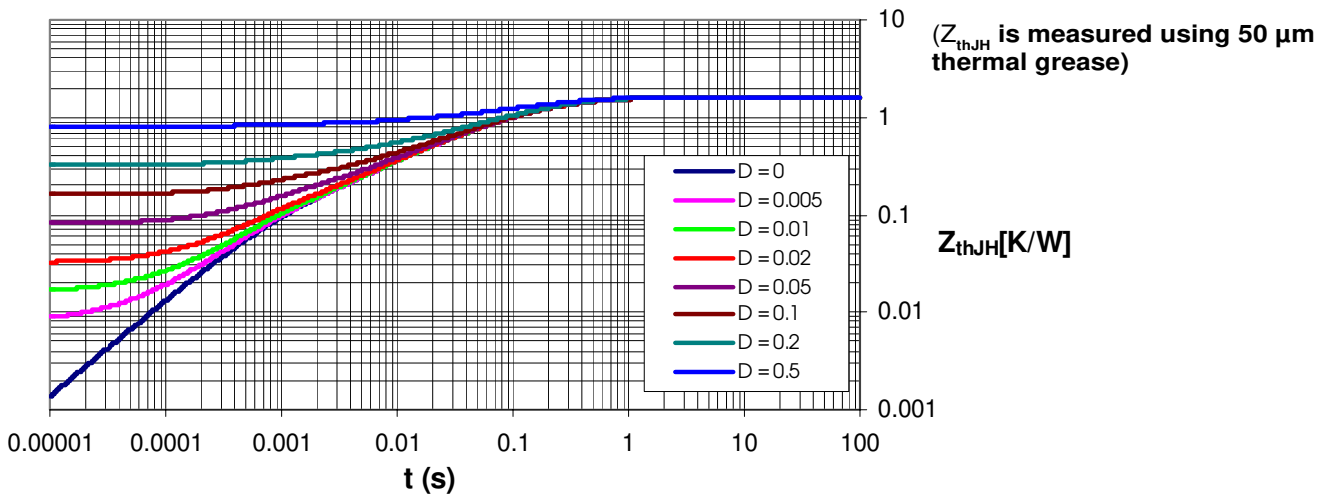
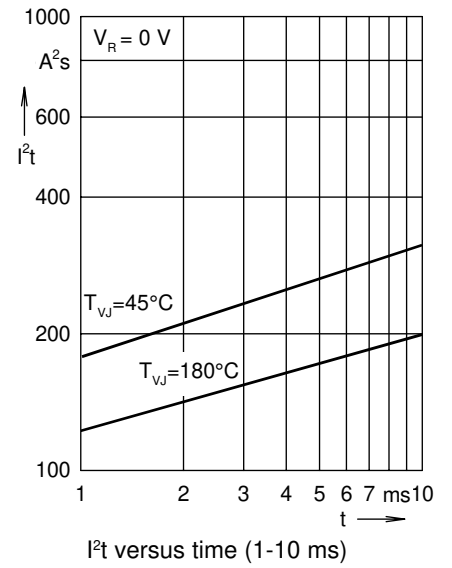
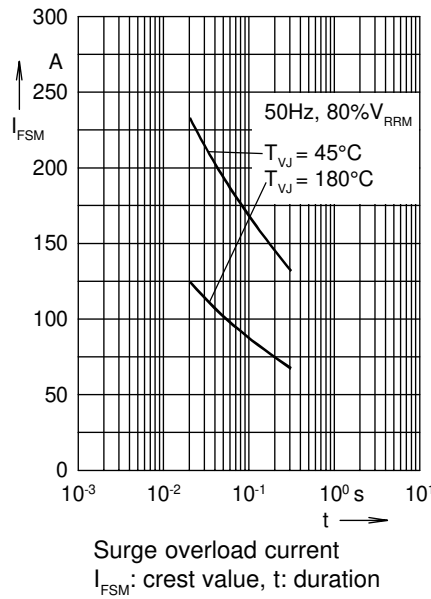
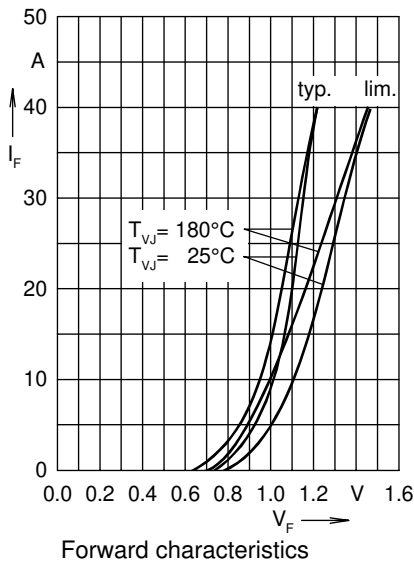
**Temperature Sensor R**

Symbol	Conditions	Maximum Ratings	
R	$T_{amb} = 20^\circ\text{C}$	4.7	kΩ

For additional data see C620/4.7k 5% S+M NTC thermistor catalog

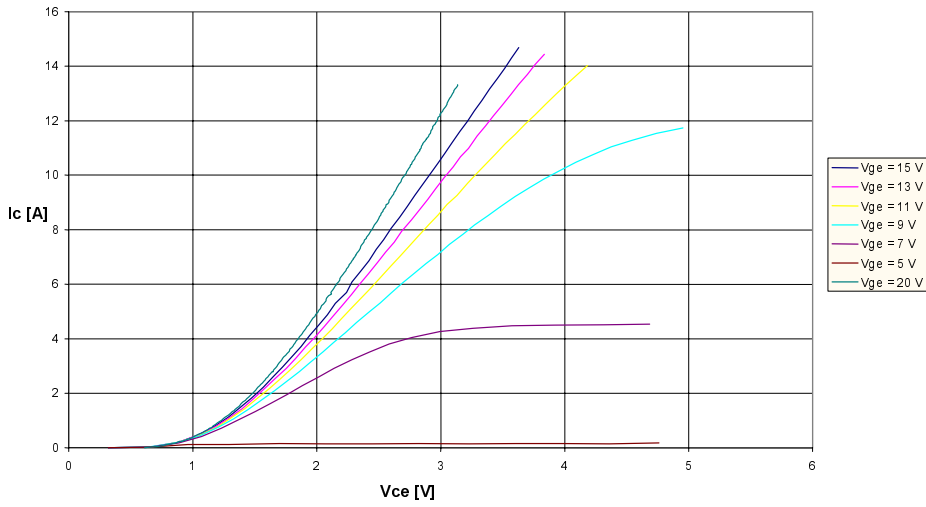


**Input Rectifier Bridge D8 - D13**

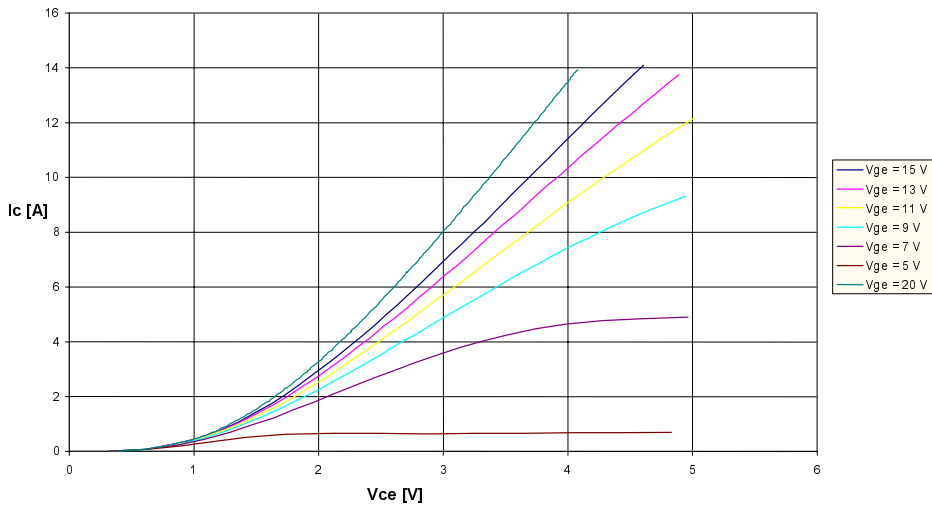


## Output Inverter T1 - T6, D1 - D6

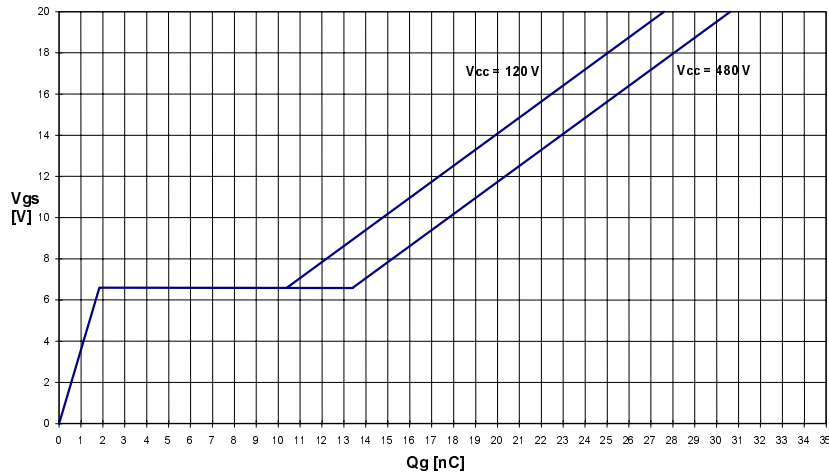
Typ. Output characteristics, 25°C



Typ. Output characteristics, 125°C

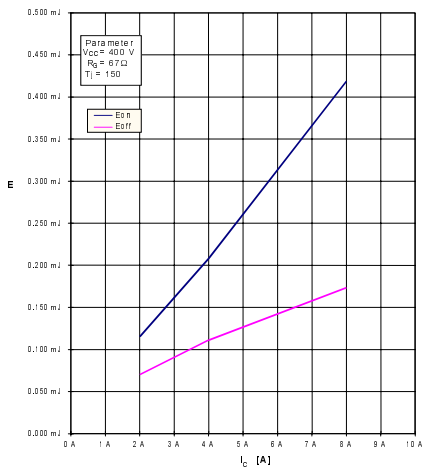


Typ. Gate-Charge

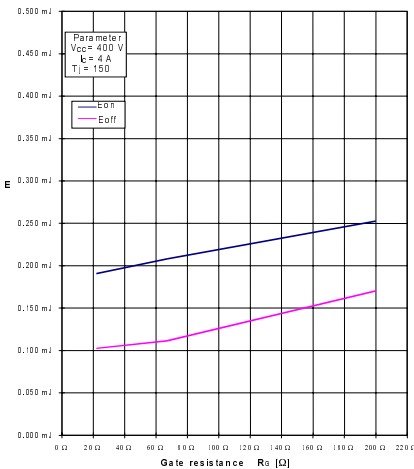


## Output Inverter T1 - T6, D1 - D6

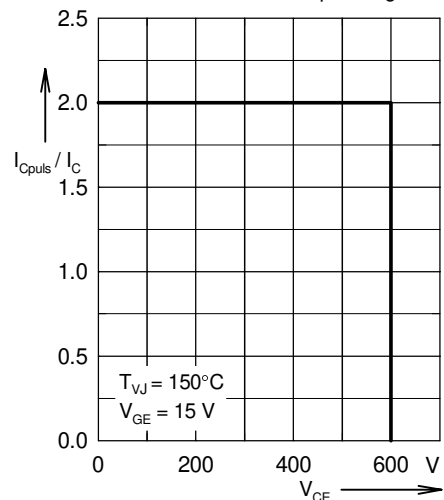
Typ. Switching losses E=f(Ic)



Typ. Switching losses E=f(Rg)

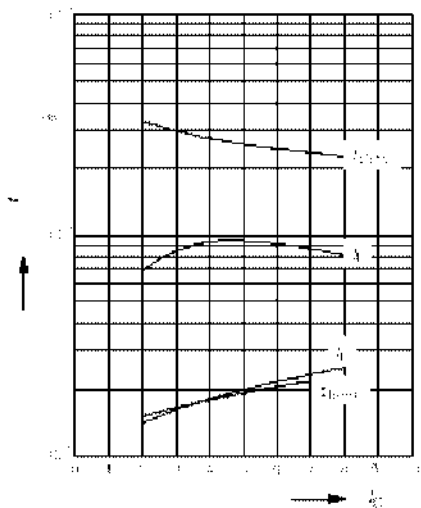


Reverse biased safe operating area



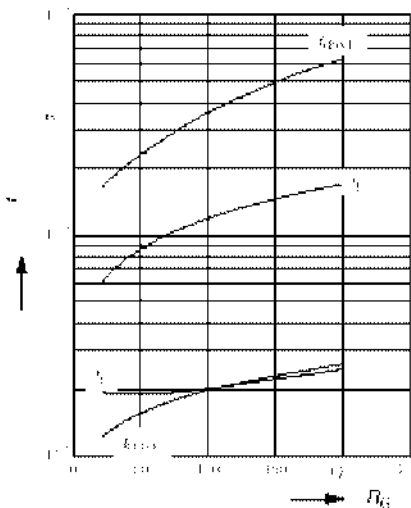
Typ. switching time

$t_{tr}$  ( $I_{C1}$ ) inductive load,  $T_j = 150^\circ\text{C}$   
 par:  $V_{CE} = 400\text{ V}$ ,  $V_{GE} = 0-15\text{ V}$ ,  $R_g = 67\ \Omega$

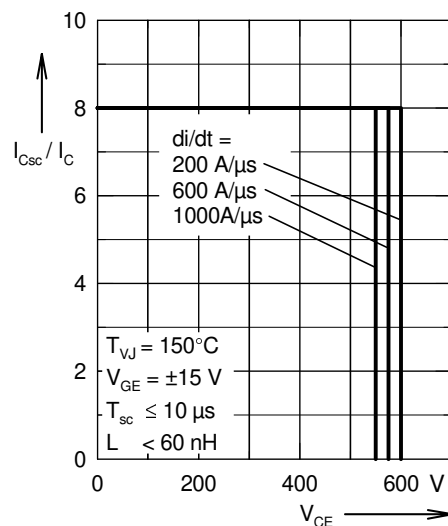


Typ. switching time

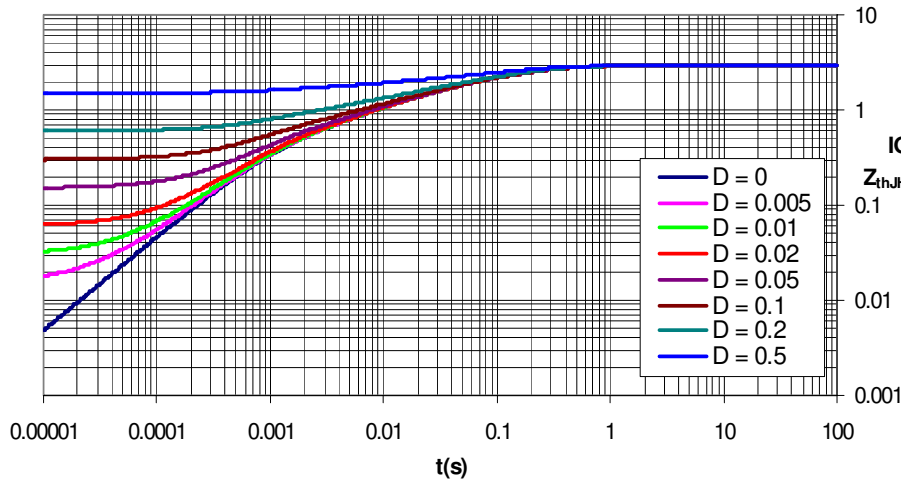
$t_{tr}$  ( $I_{C2}$ ) inductive load,  $T_j = 150^\circ\text{C}$   
 par:  $V_{CE} = 400\text{ V}$ ,  $V_{GE} = 0-15\text{ V}$ ,  $I_C = 4\text{ A}$



Short circuit safe operating area



Transient thermal resistance junction to heatsink

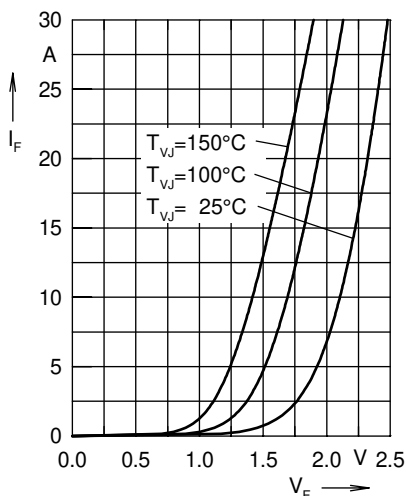


( $Z_{thjH}$  is measured using 50  $\mu\text{m}$  thermal grease)

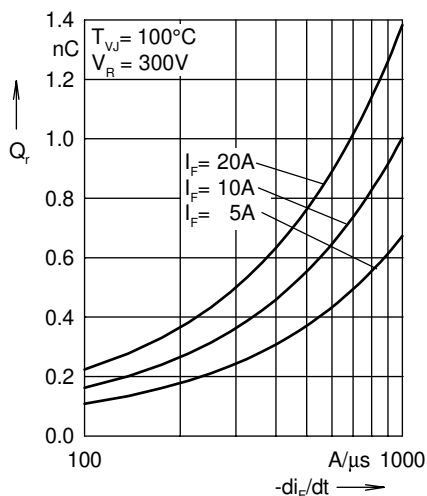
IGBT  
 $Z_{thjH}[\text{K/W}]$



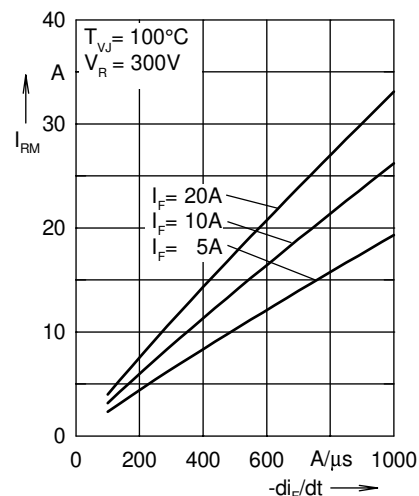
## Output Inverter D1 - D6



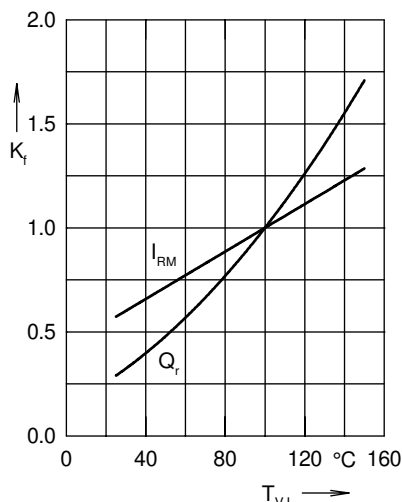
Forward current  $I_F$  versus  $V_F$



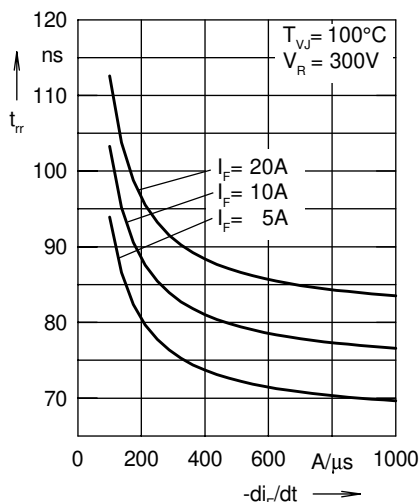
Reverse recovery charge  $Q_r$  versus  $-di_F/dt$



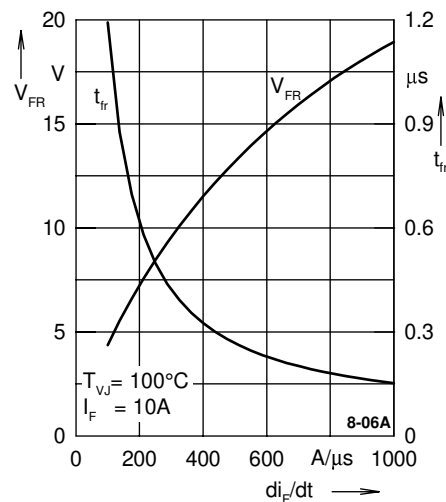
Peak reverse current  $I_{RM}$  versus  $-di_F/dt$



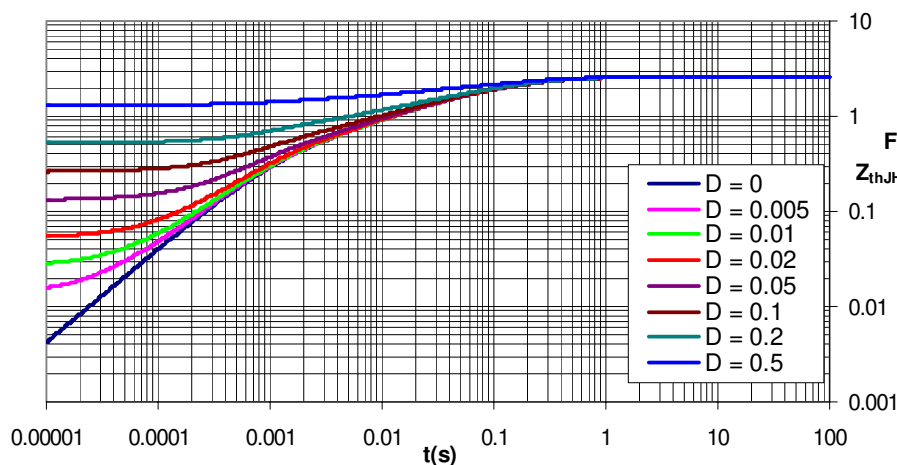
Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$



Recovery time  $t_{rr}$  versus  $-di_F/dt$



Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$



Transient thermal resistance junction to heatsink

( $Z_{thJH}$  is measured using 50  $\mu\text{m}$  thermal grease)

Fred  
 $Z_{thJH}[\text{K/W}]$

- D = 0
- D = 0.005
- D = 0.01
- D = 0.02
- D = 0.05
- D = 0.1
- D = 0.2
- D = 0.5